

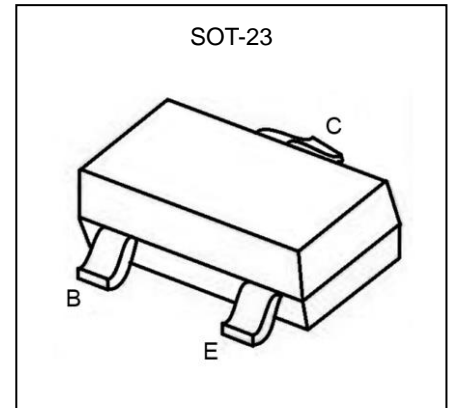


MMBTA92 Transistor(PNP)

Feature

- High Voltage Transistor

Marking: 2D



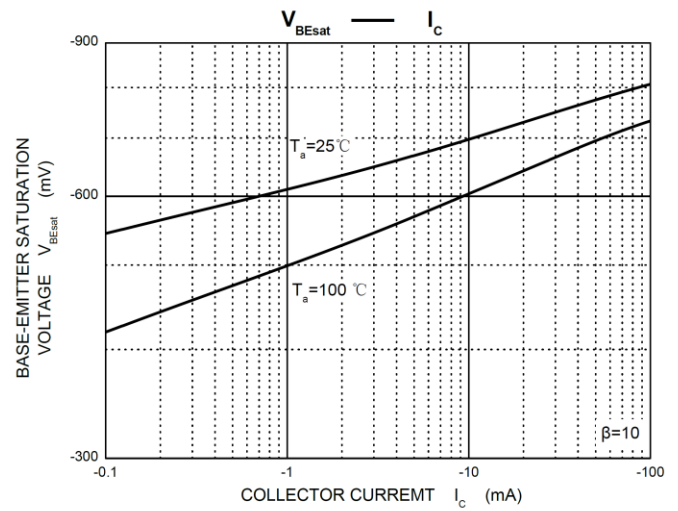
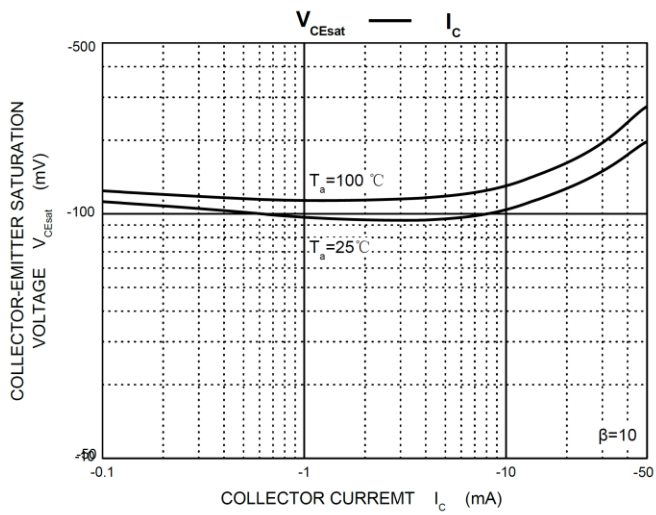
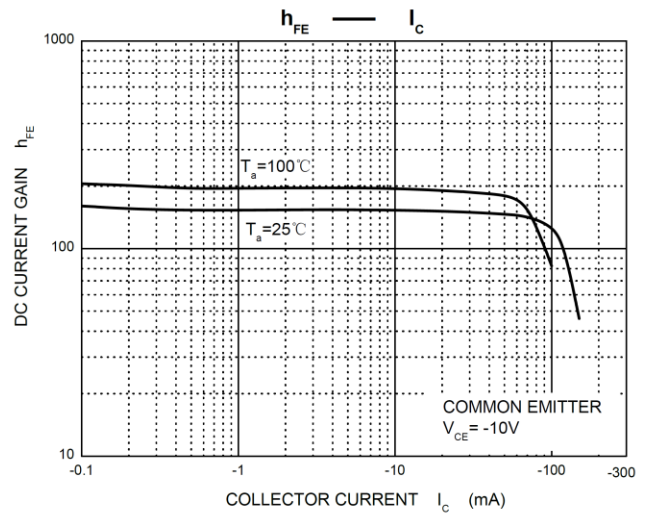
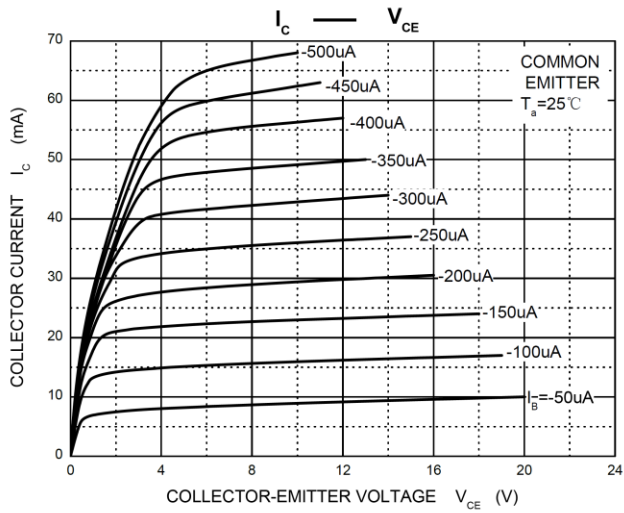
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Pulsed	I _{CM}	-0.5	A
Power Dissipation	P _d	0.625	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

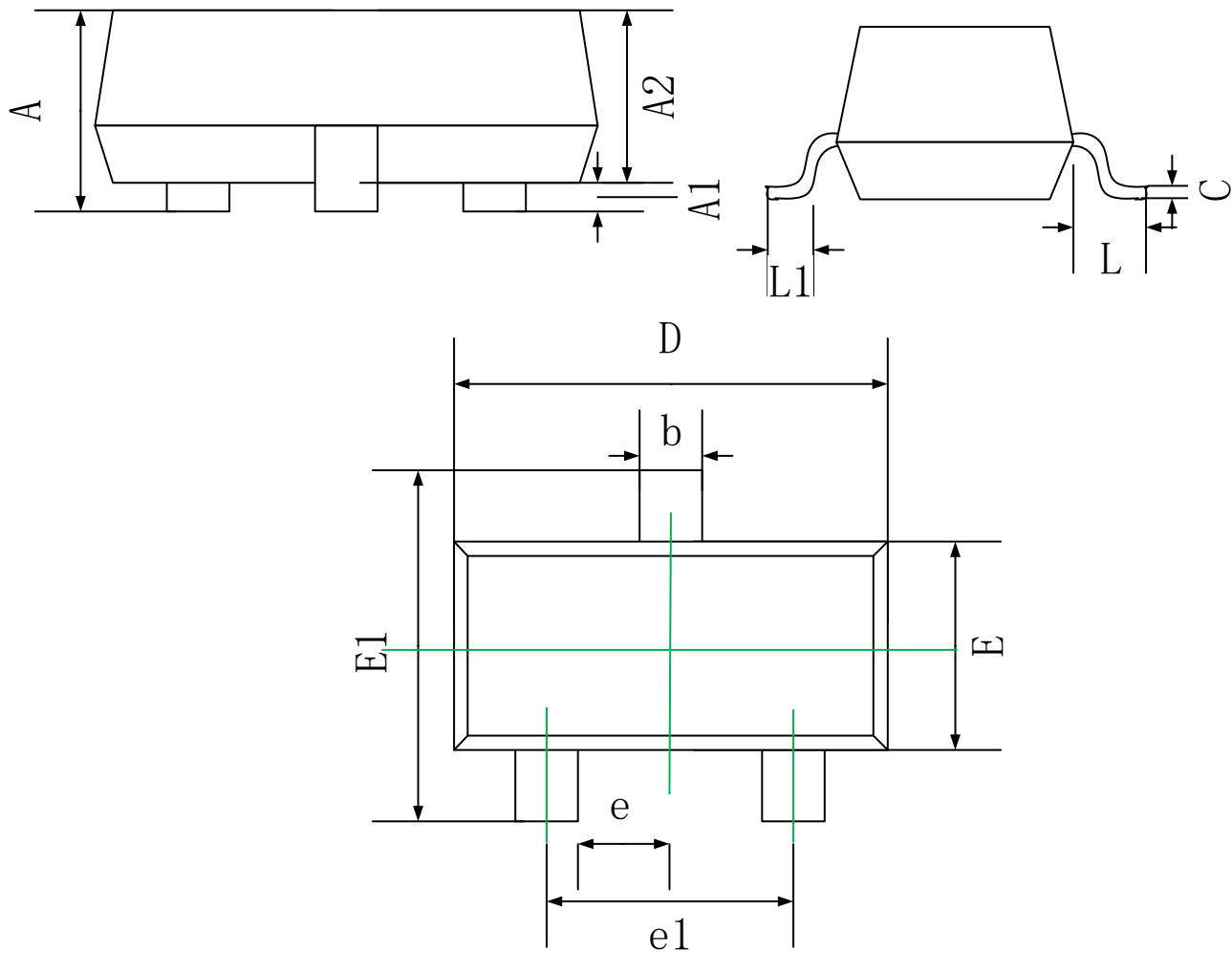
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-300		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-100μA, I _B =0	-300		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-200V, I _E =0		-500	nA
Collector cut-off current	I _{CEO}	V _{CE} =-200V, I _B =0		-500	nA
Base cut-off current	I _{EBO}	V _{EE} =-5V, I _C =0		-100	nA
DC current gain	h _{FE}	V _{CE} =-10V, I _C =-10mA	100	200	
		V _{CE} =-10V, I _C =-1mA	55		
		V _{CE} =-10V, I _C =-30mA	55		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20mA, I _B =-2mA		-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-20mA, I _B =-2mA		-0.9	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f =30MHz	50		MHZ

Typical Characteristics



SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50